

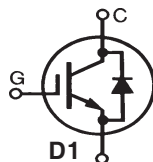
High Speed IGBT with Diode

Short Circuit SOA Capability

IXSH 10N60B2D1
IXSQ 10N60B2D1

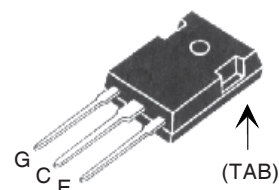
$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 20 \text{ A} \\ V_{CE(sat)} &= 2.5 \text{ V} \end{aligned}$$

Preliminary Data Sheet

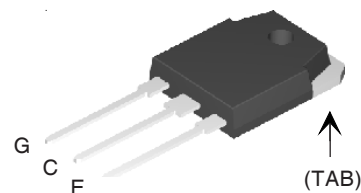


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	20	A
I_{C110}	$T_C = 110^\circ\text{C}$	10	A
$I_{F(110)}$		11	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	30	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 82 \Omega$ Clamped inductive load, $V_{CE} = 20 \text{ V}$	$I_{CM} = 20$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15 \text{ V}$, $V_{CE} = 360 \text{ V}$, $T_J = 125^\circ\text{C}$ $R_G = 150 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{slg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.3/10 Nm/lb. in	
Weight	TO-247	5	g
	TO-3P	5	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 (IXSH)



TO-3P (IXSQ)



G = Gate C = Collector
E = Emitter TAB = Collector

Features

- International standard package
- Guaranteed Short Circuit SOA capability
- Low $V_{CE(sat)}$
 - for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
 - drive simplicity
- Fast fall time for switching speeds up to 20 kHz

Applications

- AC motor speed control
- Uninterruptible power supplies (UPS)
- Welding

Advantages

- High power density

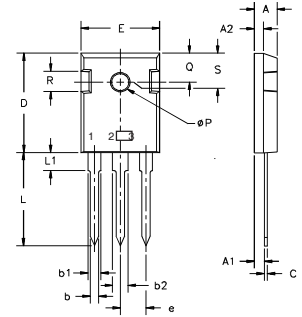
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}$, $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 750 \mu\text{A}$, $V_{CE} = V_{GE}$	4.0		7.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$			75 μA 200 μA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 10 \text{ A}$, $V_{GE} = 15 \text{ V}$			2.5 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = 10\text{A}; V_{CE} = 10\text{V}$, Note 1	2.0	3.6	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$ $f = 1\text{MHz}$		400	pF
C_{oes}			50	pF
C_{res}			11	pF
Q_g	$I_C = 10\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 V_{CES}$		17	nC
Q_{ge}			6	nC
Q_{gc}			7.5	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$		30	ns
t_{ri}	$I_C = 10\text{A}, V_{GE} = 15\text{V}$		30	ns
$t_{d(off)}$	$V_{CE} = 0.8 V_{CES}, R_G = 30\ \Omega$		180	ns
t_{fi}	Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		165	ns
E_{off}			430	750 μJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$		30	ns
t_{ri}	$I_C = 10\text{A}, V_{GE} = 15\text{V}$		30	ns
E_{on}	$V_{CE} = 0.8 V_{CES}, R_G = 30\ \Omega$		0.32	mJ
$t_{d(off)}$	Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		260	ns
t_{fi}			270	ns
E_{off}			790	μJ
R_{thJC}				1.25 K/W
R_{thCS}			0.25	K/W

Reverse Diode (FRED)		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
V_F	$I_F = 10\text{A}, V_{GE} = 0\text{V}$	$T_J = 150^\circ\text{C}$		1.66 V 2.66 V
I_{RM}	$I_F = 12\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$	$T_J = 100^\circ\text{C}$	1.5	A
t_{rr}	$V_R = 100\text{V}$	$T_J = 100^\circ\text{C}$	90	ns
t_{rr}	$I_F = 1\text{A}; -di/dt = 100\text{A}/\mu\text{s}; V_R = 30\text{V}$		25	ns
R_{thJC}				2.5 K/W

Note 1: Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

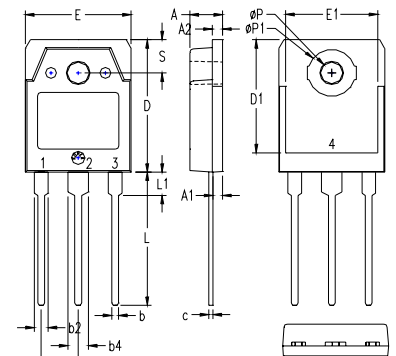
TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.7 5.3	.185 .209
A ₁	2.2 2.54	.087 .102
A ₂	2.2 2.6	.059 .098
b	1.0 1.4	.040 .055
b ₁	1.65 2.13	.065 .084
b ₂	2.87 3.12	.113 .123
C	.4 .8	.016 .031
D	20.80 21.46	.819 .845
E	15.75 16.26	.610 .640
e	5.20 5.72	0.205 0.225
L	19.81 20.32	.780 .800
L ₁	4.50	.177
ØP	3.55 3.65	.140 .144
Q	5.89 6.40	0.232 0.252
R	4.32 5.49	.170 .216
S	6.15 BSC	.242 BSC

TO-3P Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

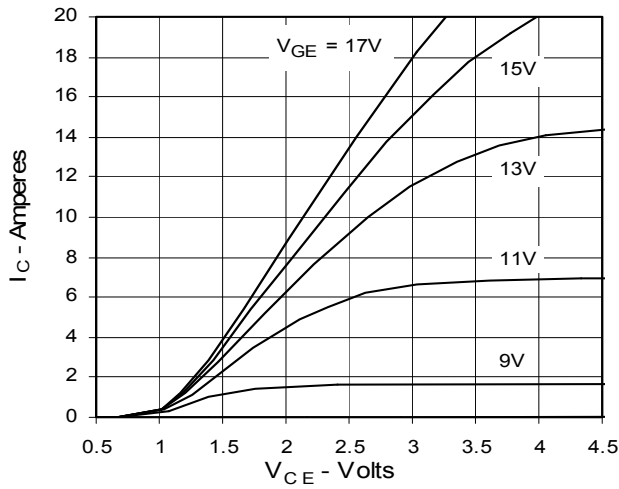
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A ₁	.051	.059	1.30	1.50
A ₂	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b ₂	.075	.087	1.90	2.20
b ₄	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D ₁	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E ₁	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L ₁	.134	.142	3.40	3.60
ØP	.126	.134	3.20	3.40
ØP ₁	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal area are tin plated.

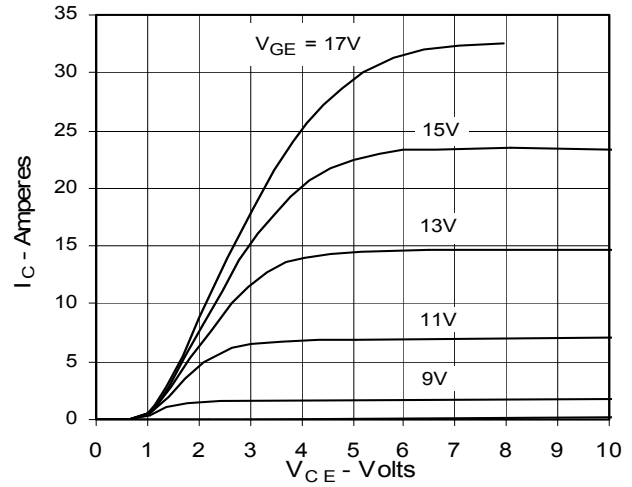
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

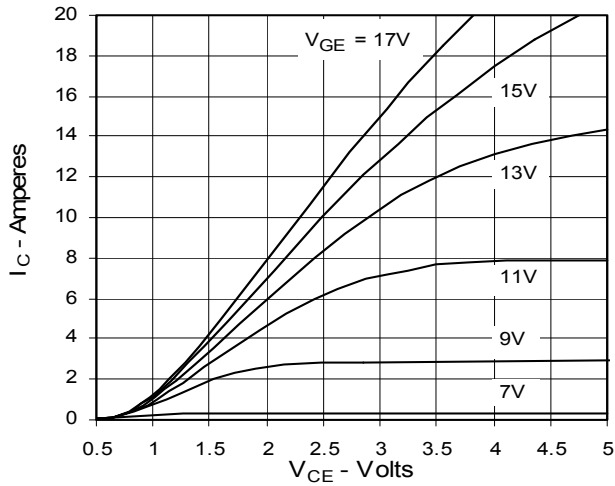
**Fig. 1. Output Characteristics
@ 25 °C**



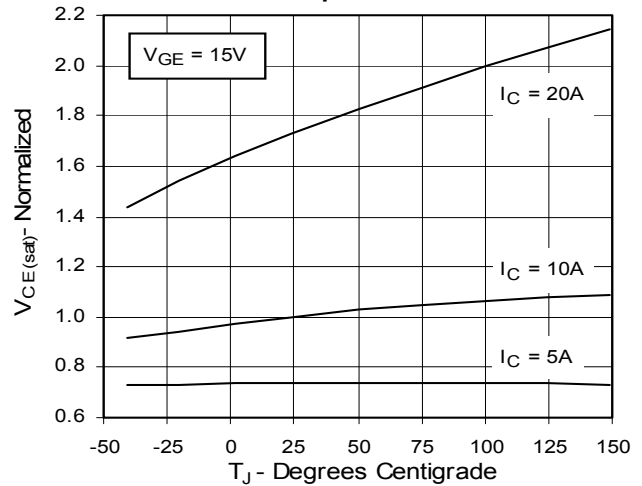
**Fig. 2. Extended Output Characteristics
@ 25 °C**



**Fig. 3. Output Characteristics
@ 125 °C**



**Fig. 4. Dependence of $V_{CE(sat)}$ on
Temperature**



**Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter voltage**

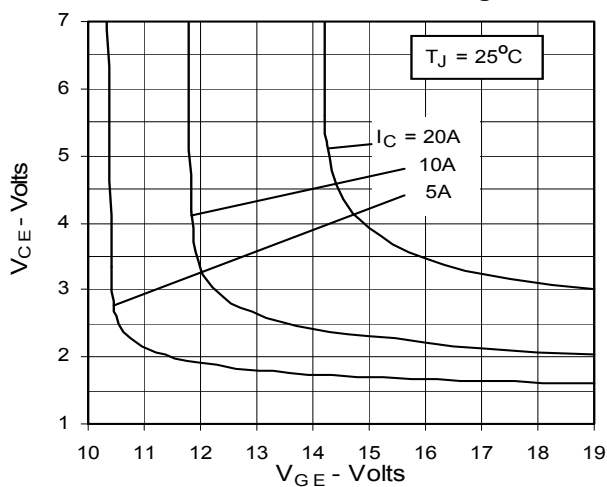


Fig. 6. Input Admittance

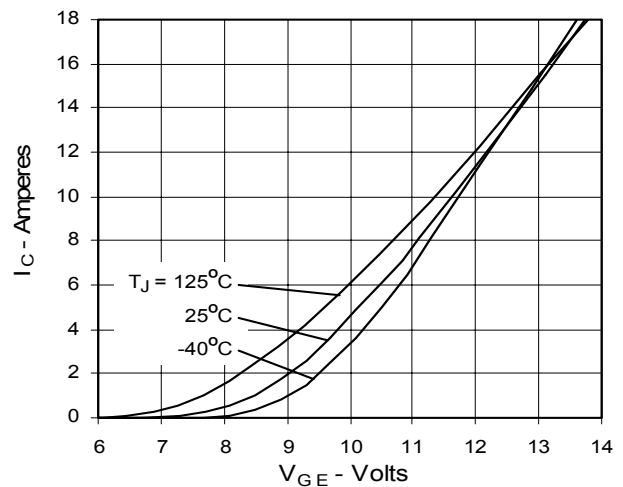


Fig. 7. Transconductance

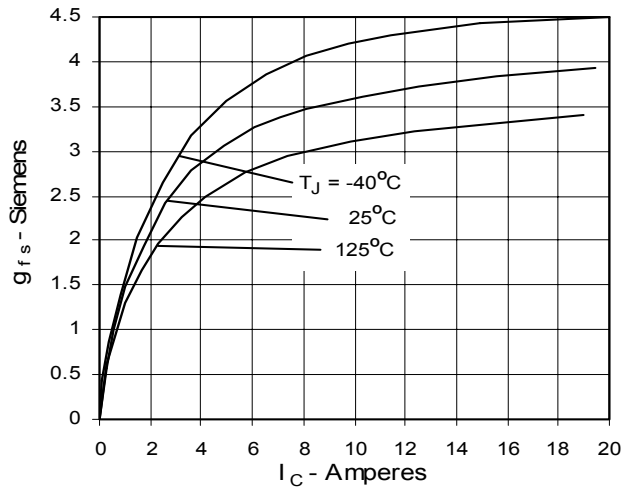


Fig. 8. Dependence of Turn-off Energy Loss on R_G

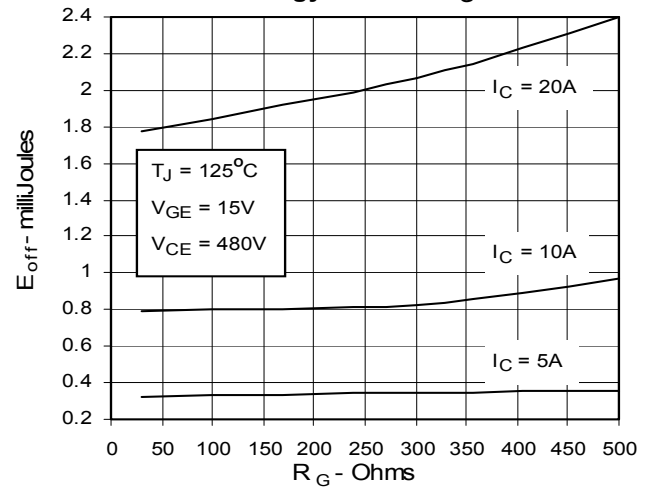


Fig. 9. Dependence of Turn-Off Energy Loss on I_C

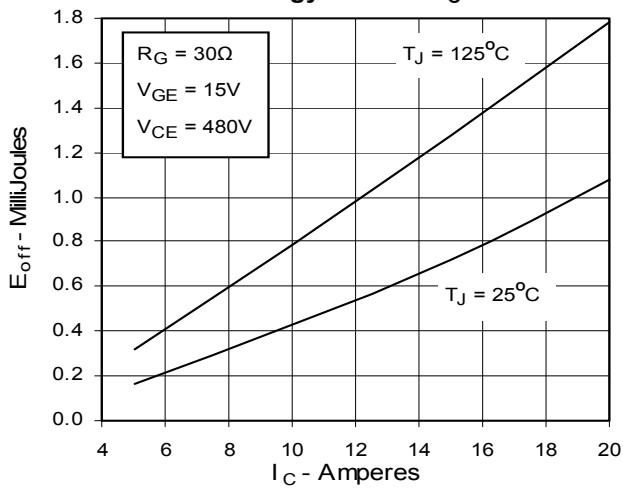


Fig. 10. Dependence of Turn-off Energy Loss on Temperature

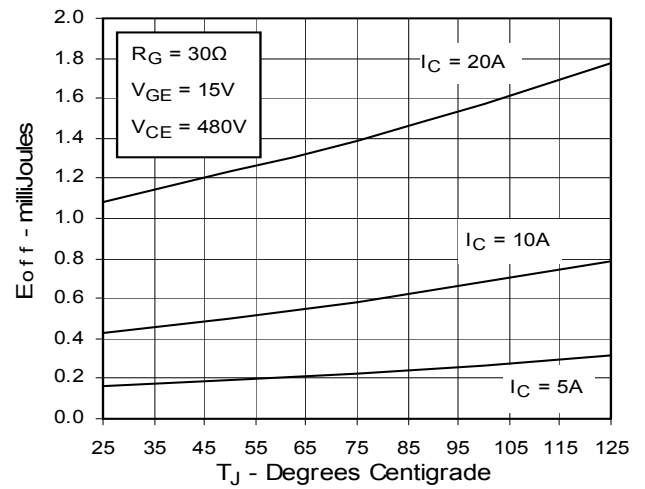


Fig. 11. Dependence of Turn-off Switching Time on R_G

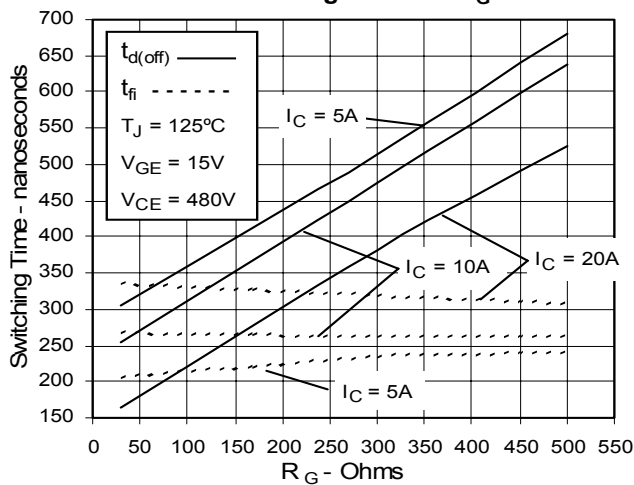


Fig. 12. Dependence of Turn-off Switching Time on I_C

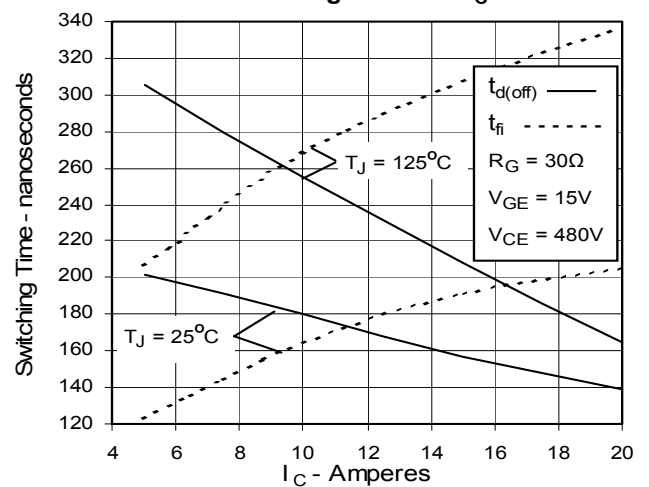


Fig. 13. Dependence of Turn-off Switching Time on Temperature

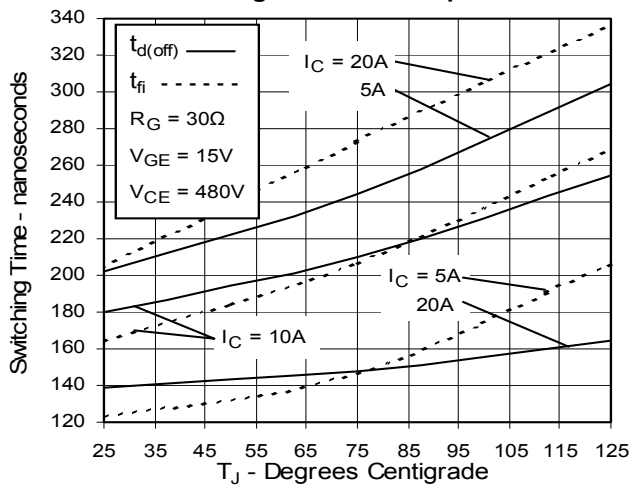


Fig. 14. Gate Charge

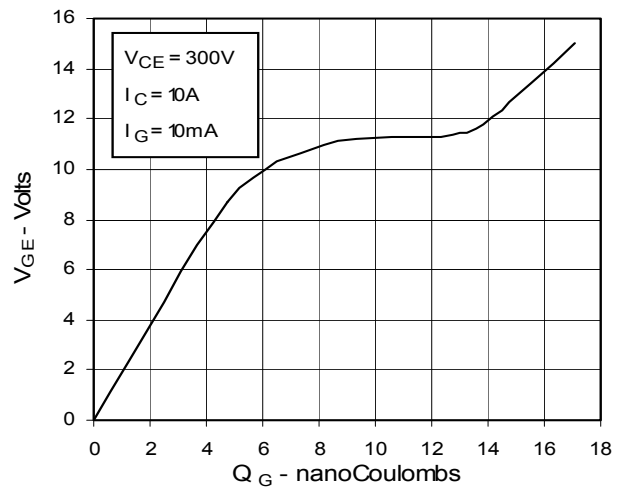


Fig. 15. Capacitance

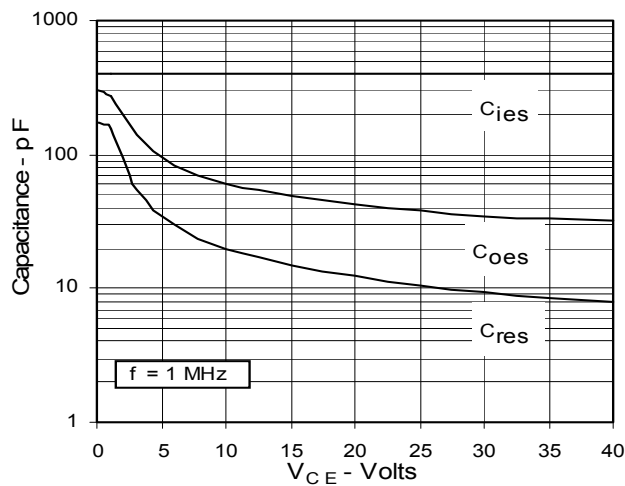


Fig. 16. Reverse-Bias Safe Operating Area

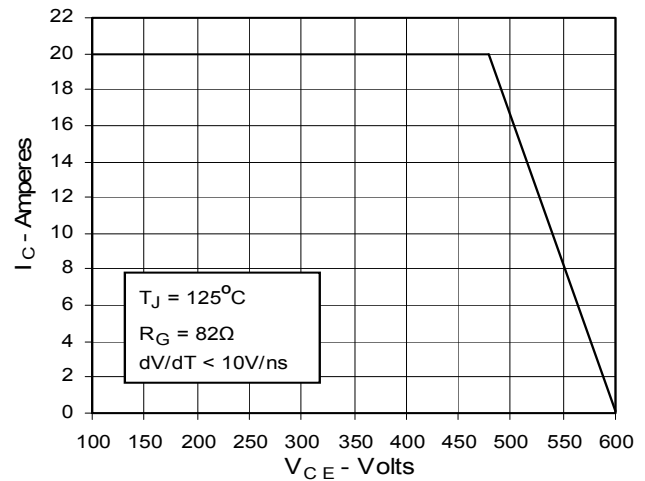
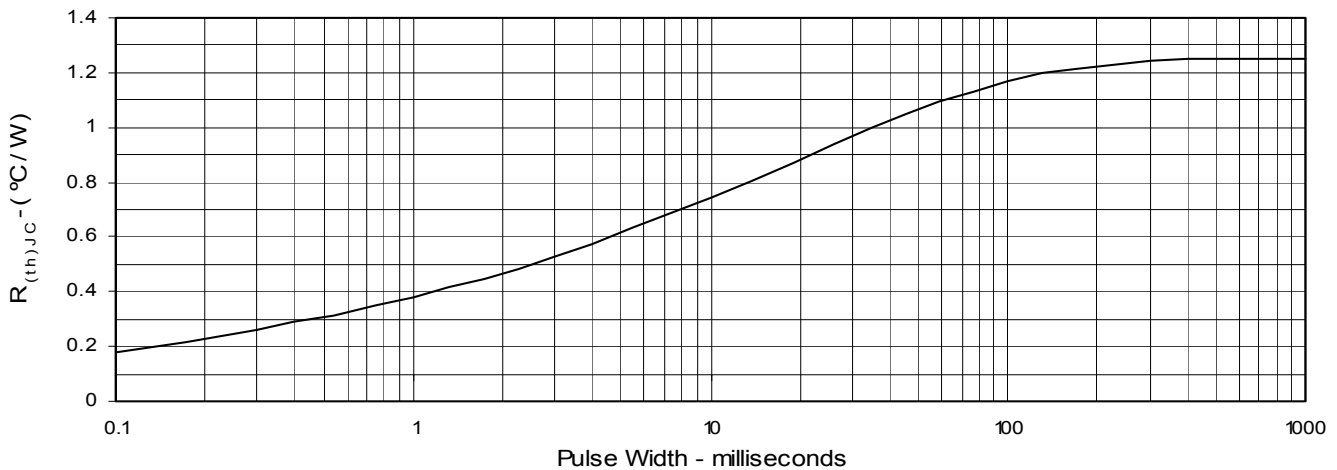


Fig. 17. Maximum Transient Thermal Resistance



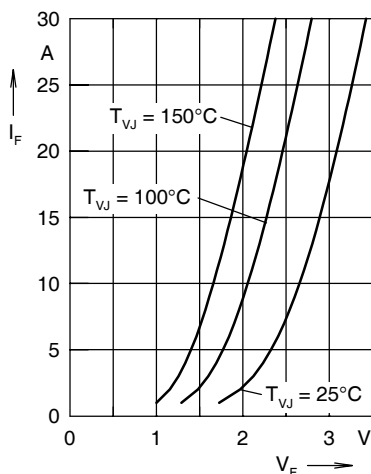


Fig. 18. Forward current I_F versus V_F

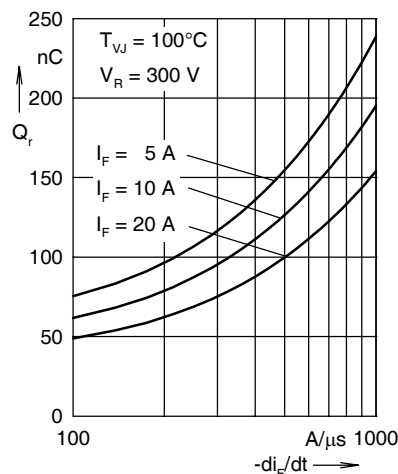


Fig. 19. Reverse recovery charge Q_r versus $-di_F/dt$

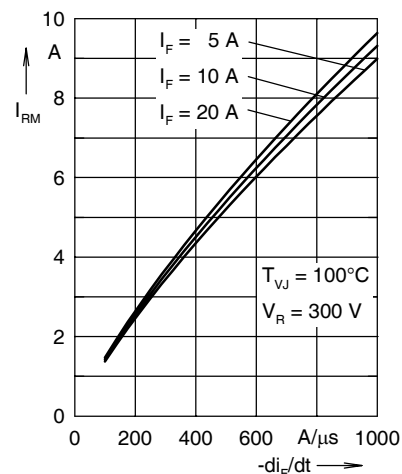


Fig. 20. Peak reverse current I_{RM} versus $-di_F/dt$

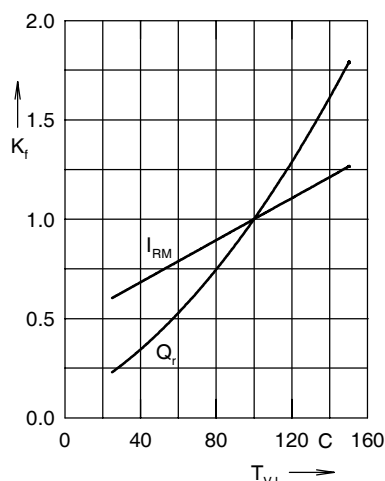


Fig. 21. Dynamic parameters Q_r , I_{RM} versus T_{VJ}

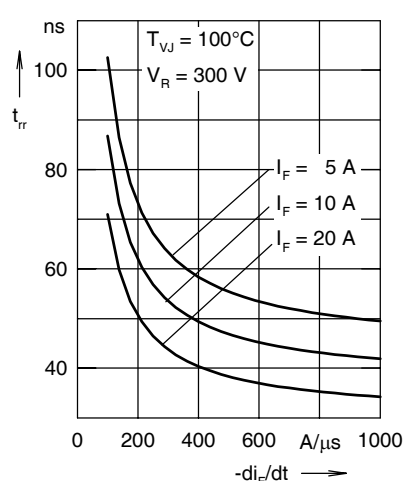


Fig. 22. Recovery time t_{rr} versus $-di_F/dt$

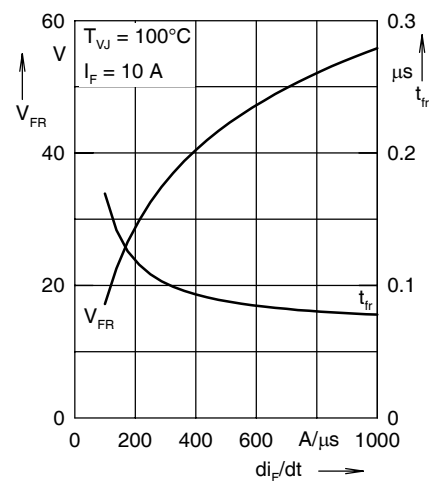


Fig. 23. Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

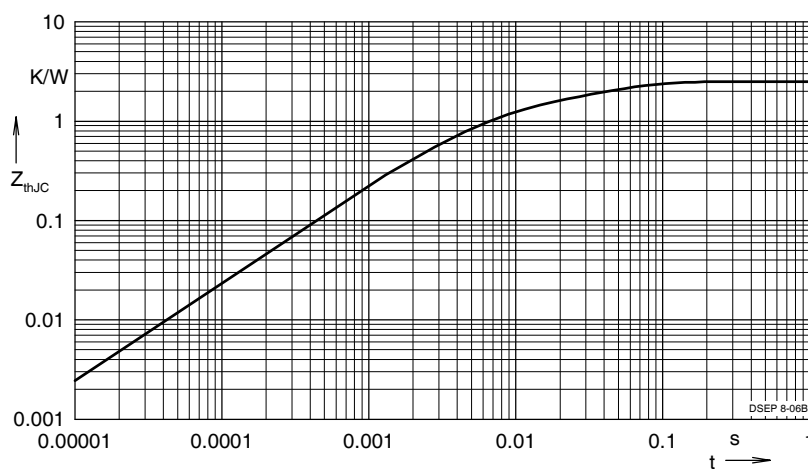


Fig. 24. Transient thermal resistance junction-to-case

NOTE: Fig. 19 to Fig. 23 shows typical values

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	1.449	0.0052
2	0.5578	0.0003
3	0.4931	0.0169

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